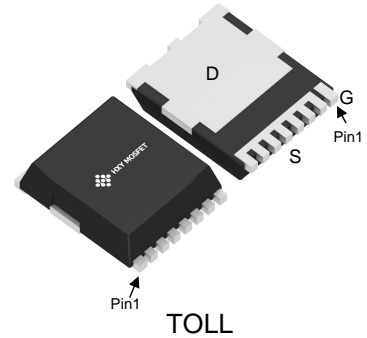




General Description

The HT7202 use advanced SGT MOSFET technology to provide low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness.



General Features

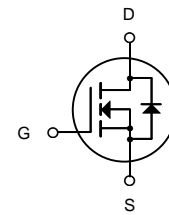
$V_{DS} = 80V$ $I_D = 400A$

$R_{DS(ON)} < 2m\Omega @ V_{GS}=10V$

Applications

Battery Protection

Power Distribution



N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HT7202	TOLL	HXY MOSFET	2000

Absolute Maximum Ratings at $T_J=25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	400
		$T_C=100^\circ C$	253
Pulsed Drain Current ¹	I_{DM}	1600	A
Single Pulse Avalanche Energy ²	EAS	1280	mJ
Total Power Dissipation	P_D	468.8	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ C$
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	39	$^\circ C/W$
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	0.32	$^\circ C/W$



Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	80	-	-	V
Gate-body Leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	V _{DS} = 80V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C		-	-	100	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
Drain-Source on-Resistance ⁴	R _{DS(on)}	V _{GS} = 10V, I _D = 20A	-	1.6	2	mΩ
Forward Transconductance ⁴	g _{fs}	V _{DS} = 10V, I _D = 20A	-	70	-	S
Dynamic Characteristics⁵						
Input Capacitance	C _{iss}	V _{DS} = 40V, V _{GS} = 0V, f = 1MHz	-	8980	-	pF
Output Capacitance	C _{oss}		-	1560	-	
Reverse Transfer Capacitance	C _{rss}		-	90	-	
Gate Resistance	R _g	f=1MHz	-	2.4	-	Ω
Switching Characteristics⁵						
Total Gate Charge	Q _g	V _{GS} = 10V, V _{DS} = 40V, I _D = 20A	-	140	-	nC
Gate-Source Charge	Q _{gs}		-	37.5	-	
Gate-Drain Charge	Q _{gd}		-	37.5	-	
Turn-on Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 40V, R _G = 3Ω, I _D = 20A	-	27.5	-	ns
Rise Time	t _r		-	82	-	
Turn-off Delay Time	t _{d(off)}		-	85	-	
Fall Time	t _f		-	52	-	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20A, di/dt = 100A/μs	-	98	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	166	-	nC
Drain-Source Body Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	I _S = 20A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C =25°C	I _S	-	-	400	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.5mH, I_{AS}=50A.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

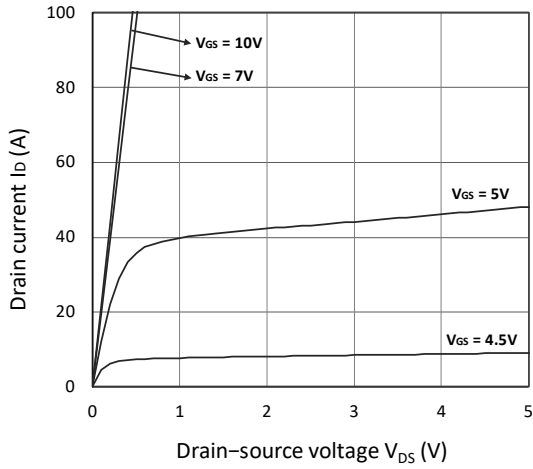


Figure 1. Output Characteristics

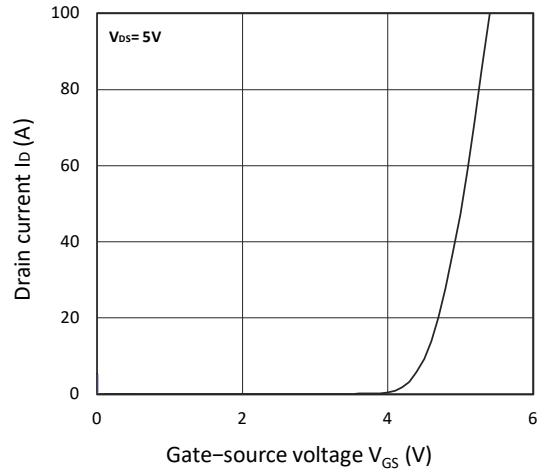


Figure 2. Transfer Characteristics

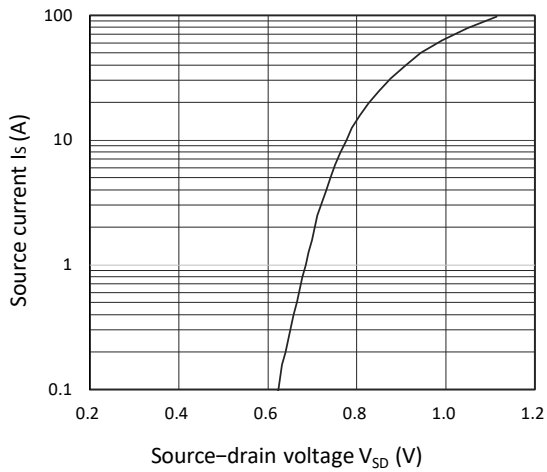


Figure 3. Forward Characteristics of Reverse

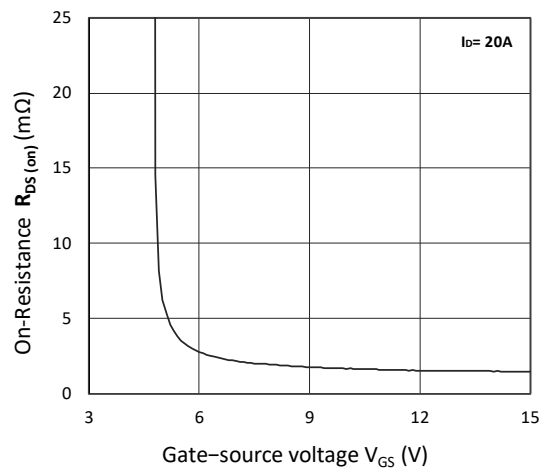


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

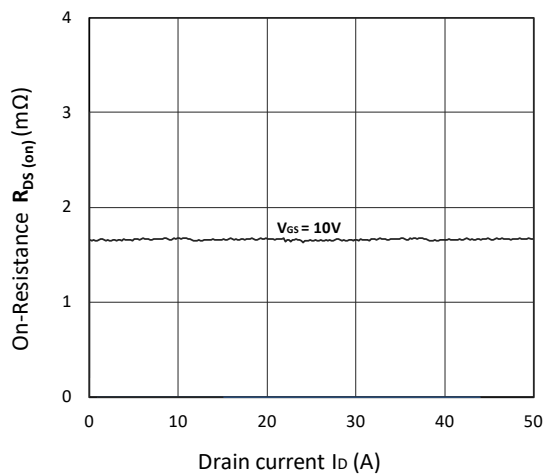


Figure 5. $R_{DS(ON)}$ vs. I_D

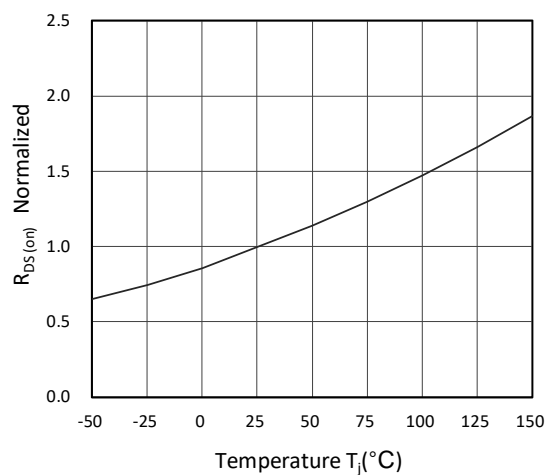


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

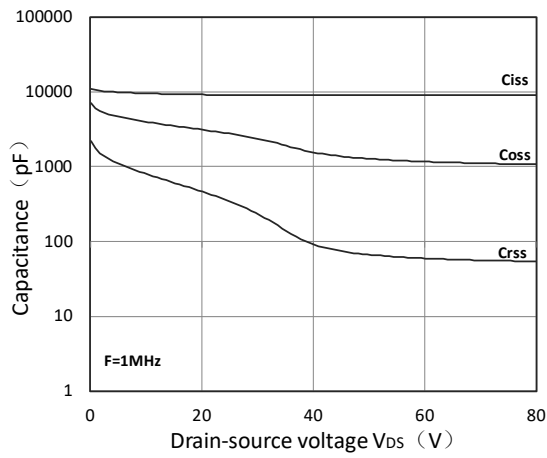


Figure 7. Capacitance Characteristics

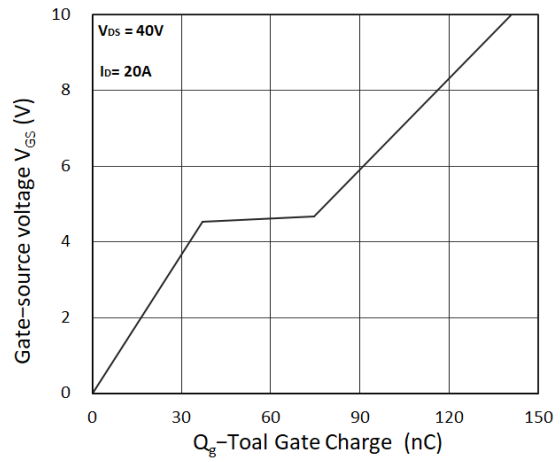


Figure 8. Gate Charge Characteristics

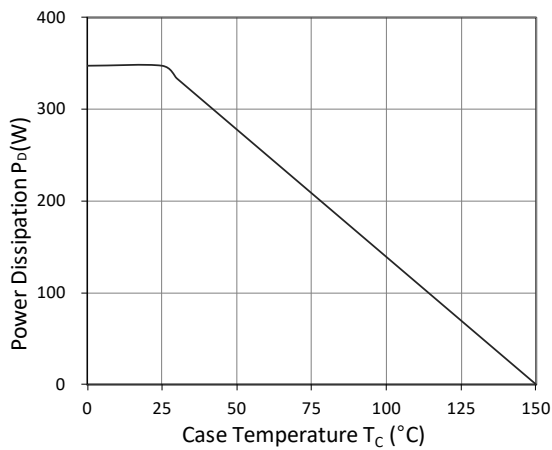


Figure 9. Power Dissipation

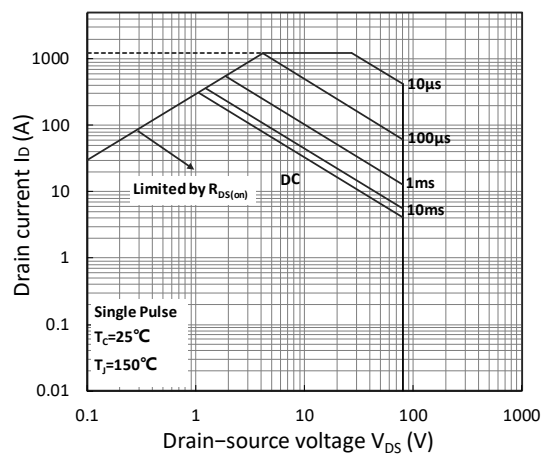


Figure 10. Safe Operating Area

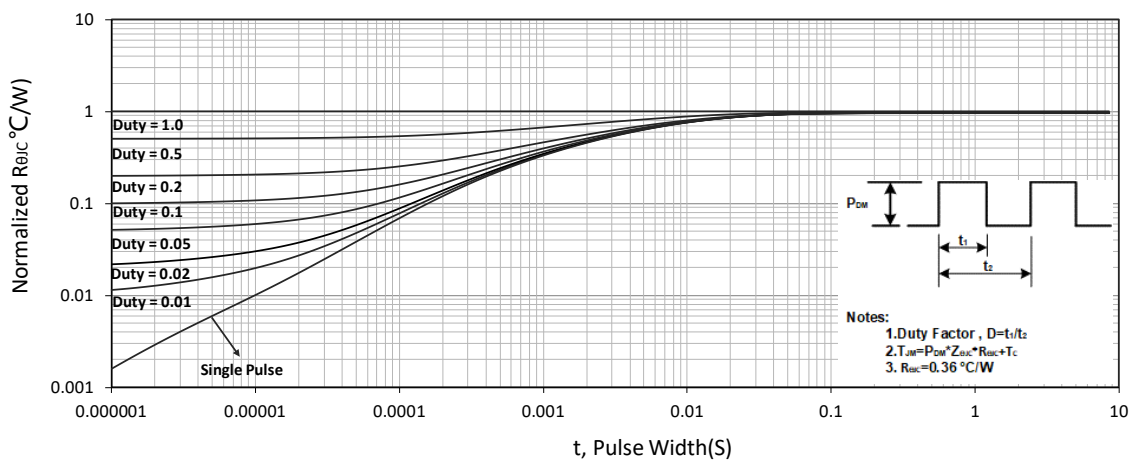


Figure 11. Normalized Maximum Transient Thermal Impedance



Test Circuit

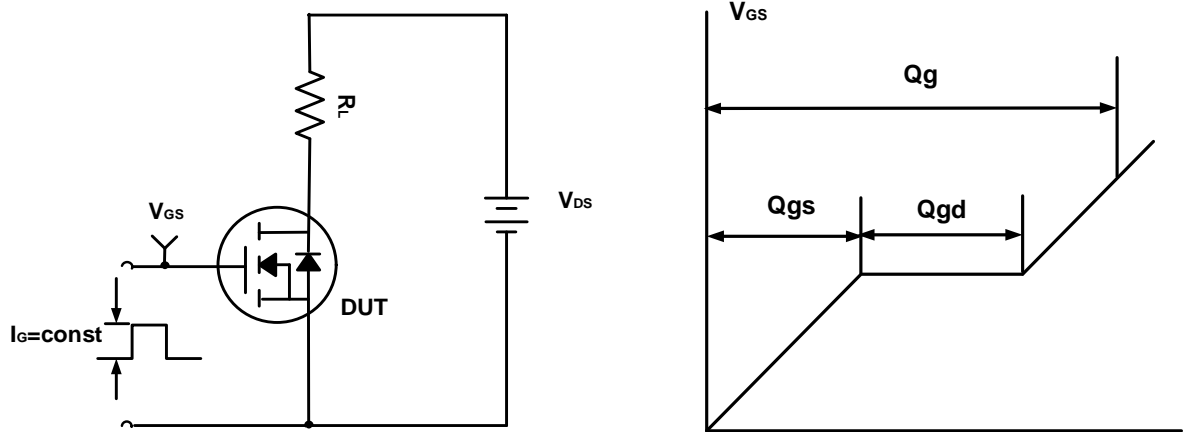


Figure A. Gate Charge Test Circuit & Waveforms

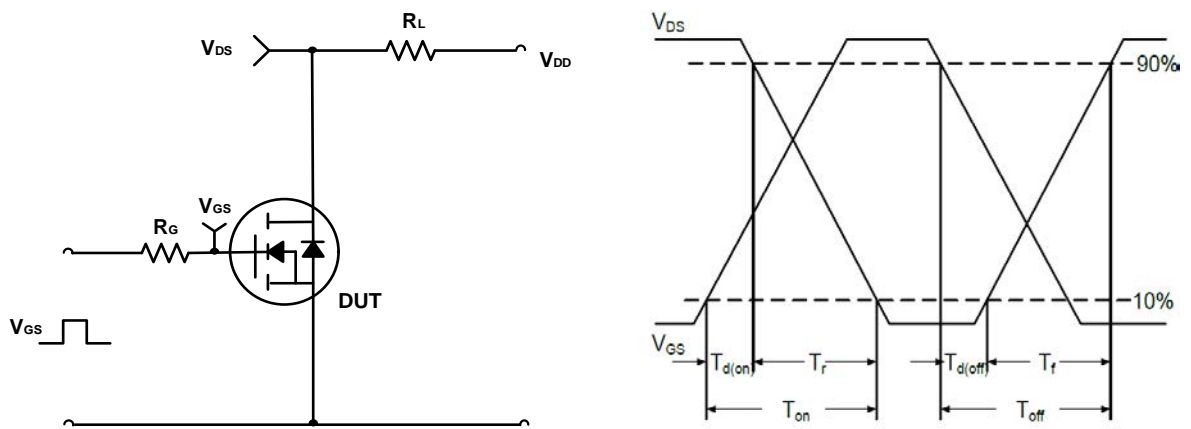


Figure B. Switching Test Circuit & Waveforms

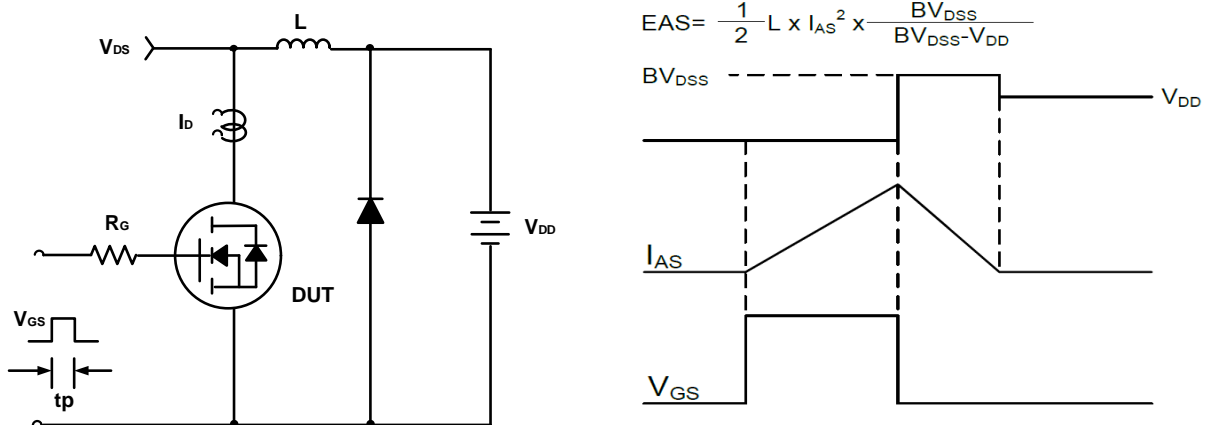
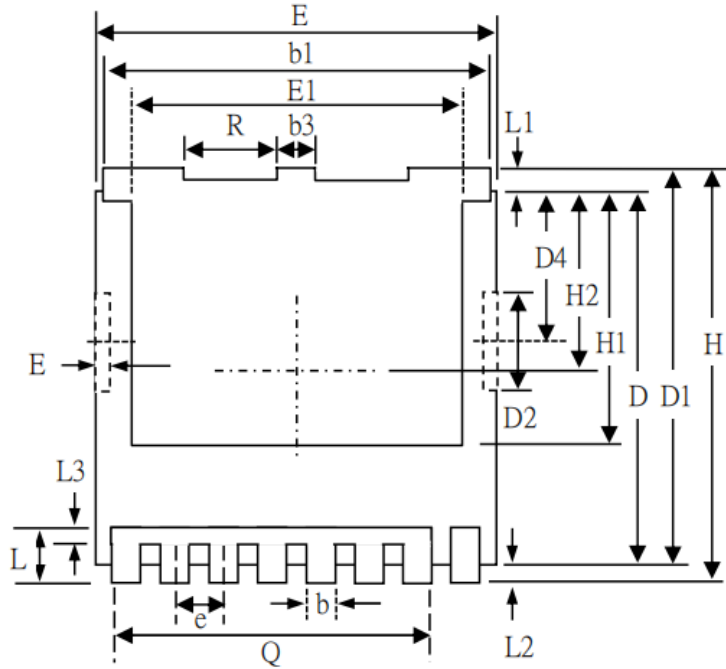


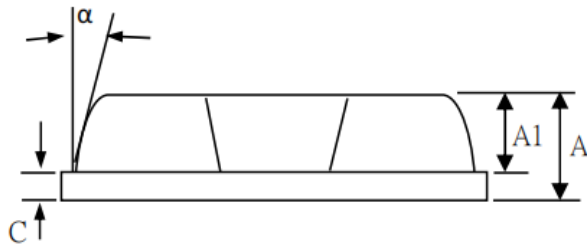
Figure C. Unclamped Inductive Switching Circuit & Waveforms



TOLL Package Information



BACKSIDE VIEW



Symbol	mm	
	Min	Max
A	2.20	2.40
b	0.60	0.90
b1	9.70	9.90
c	0.40	0.60
D	10.20	10.60
D1	3.10	3.50
D2	4.45	4.75
E	9.70	10.10
E1	7.80BSC	
E2	0.50	0.70
e	1.200 BSC	
H	11.45	11.90
H1	6.75 BSC	
K	3.10 REF	
L	1.70	2.10
L1	0.60	0.80
L2	0.50	0.70
θ	10° REF	

- 1.All Dimension Are In Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.



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